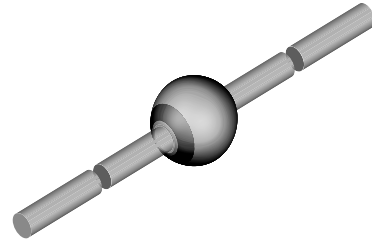


## Fast Avalanche Sinterglass Diode

### Features

- Glass passivated junction
- Hermetically sealed package
- Soft recovery characteristics
- Low reverse current
- Low forward voltage drop
- High pulse current capability



949588

### Applications

Fast rectification diode

### Mechanical Data

**Case:** Sintered solid glass body, SOD 64

**Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026

**Polarity:** Color band denotes cathode end

**Mounting Position:** Any

**Weight:** 860 mg (max. 1000 mg)

### Parts Table

Part	Type differentiation	Package
1N5417	$V_R = 200\text{ V}; I_{FAV} = 3\text{ A}$	SOD64
1N5418	$V_R = 400\text{ V}; I_{FAV} = 3\text{ A}$	SOD64

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	see electrical characteristics	1N5417	$V_R = V_{RRM}$	200	V
	see electrical characteristics	1N5418	$V_R = V_{RRM}$	400	V
Maximum average forward rectified current			$I_{F(AV)}$	3.0	A
Peak forward surge current	10 ms single half sine-wave		$I_{FSM}$	100	A
Non repetitive reverse avalanche energy	$I_{(BR)R} = 1\text{ A}$		$E_R$	20	mJ

### Maximum Thermal Resistance

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Value	Unit
Junction ambient	$l = 10\text{ mm}, T_L = \text{constant}$		$R_{thJA}$	25	K/W
	on PC board with spacing 25 mm		$R_{thJA}$	70	K/W
Operating junction and storage temperature range			$T_J, T_{STG}$	- 55 to + 175	$^\circ\text{C}$

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Min	Typ.	Max	Unit
Maximum instantaneous forward voltage	$I_F = 3\text{ A}$		$V_F$			1.10	V
	$I_F = 9\text{ A}$		$V_F$			1.50	V
Reverse current	$V_R = V_{RRM}$		$I_R$			1.0	$\mu\text{A}$
	$V_R = V_{RRM}, T_j = 100\text{ }^{\circ}\text{C}$		$I_R$			20	$\mu\text{A}$
Maximum reverse recovery time	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$		$t_{rr}$		75	100	ns

### Typical Characteristics ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

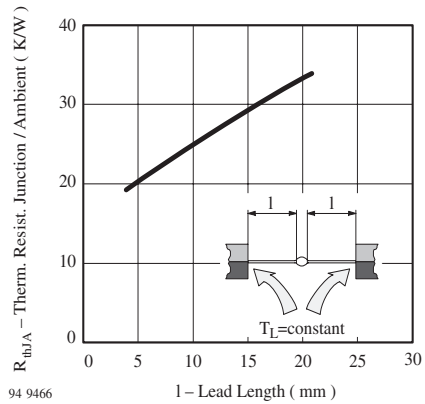


Figure 1. Max. Thermal Resistance vs. Lead Length

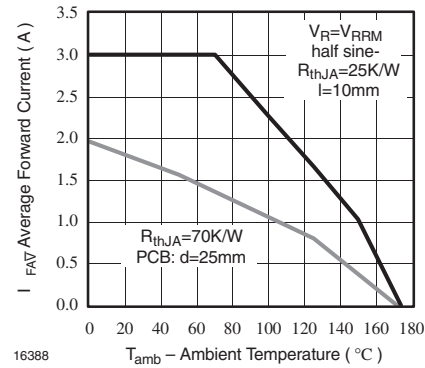


Figure 3. Max. Average Forward Current vs. Ambient Temperature

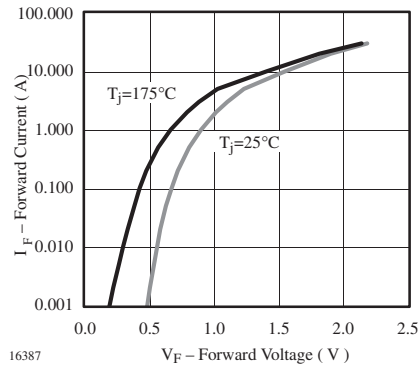


Figure 2. Forward Current vs. Forward Voltage

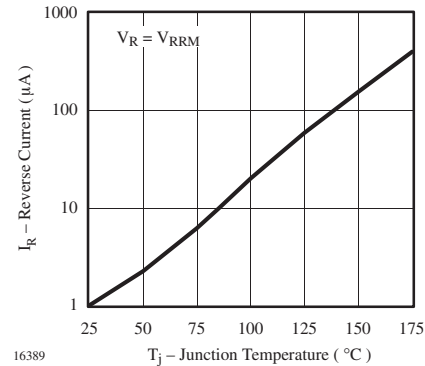


Figure 4. Reverse Current vs. Junction Temperature

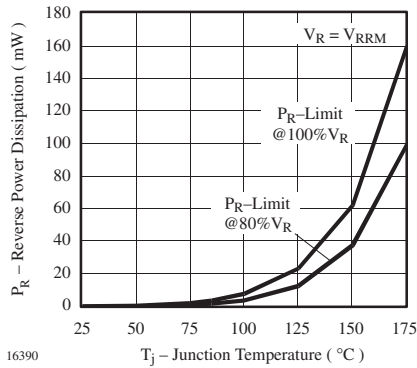


Figure 5. Max. Reverse Power Dissipation vs. Junction Temperature

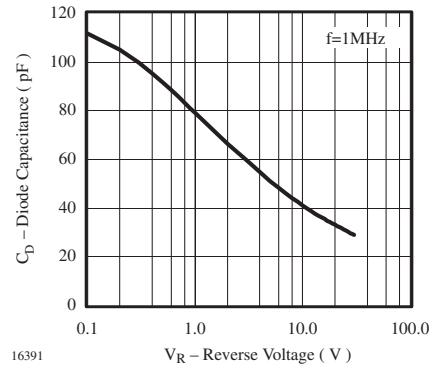


Figure 6. Diode Capacitance vs. Reverse Voltage

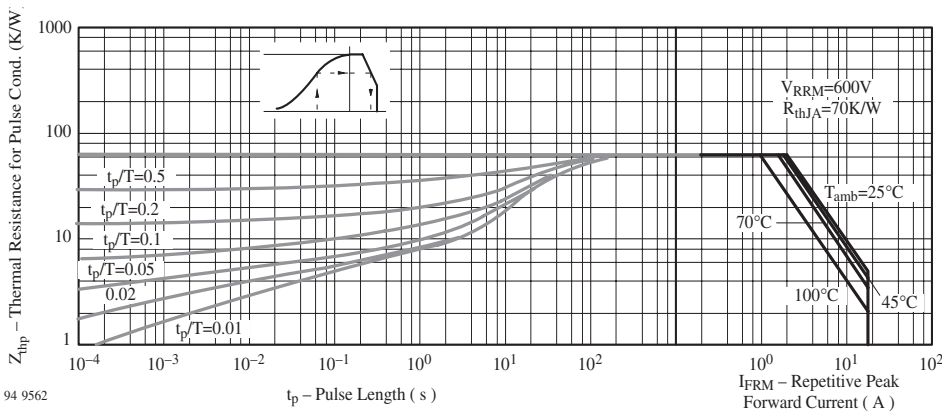
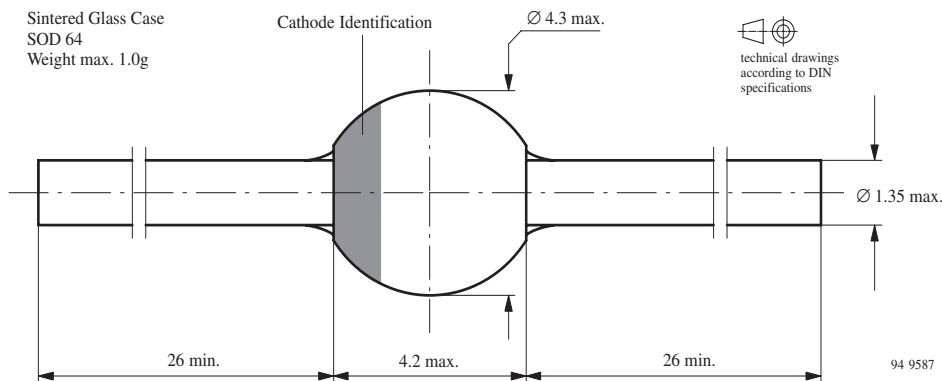


Figure 7. Thermal Response

## Package Dimensions in mm



### Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design  
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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